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Electronic Supplementary Information

Facet-Dependent Electrical Conductivity Properties of GaN Wafers

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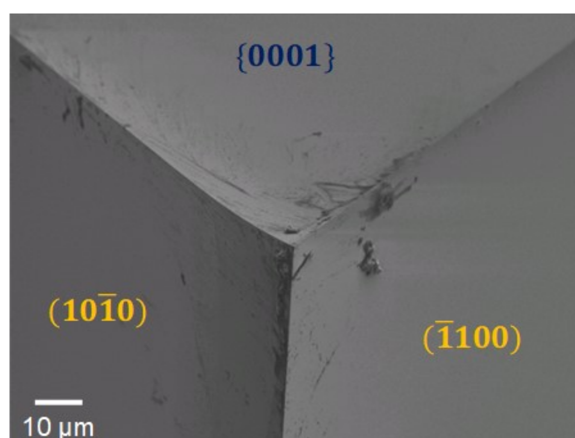

Fig. S1 SEM image of a GaN wafer that was cut and broken to expose side facets.

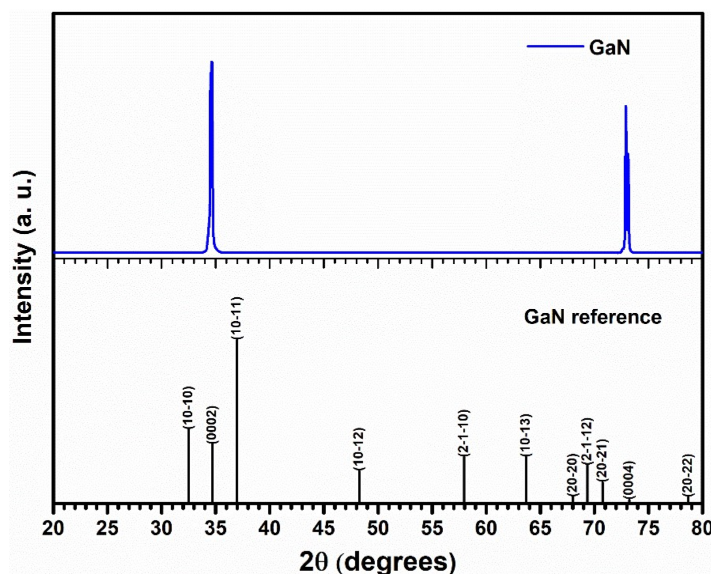

Fig. S2 XRD pattern of a GaN wafer used for conductivity measurements.

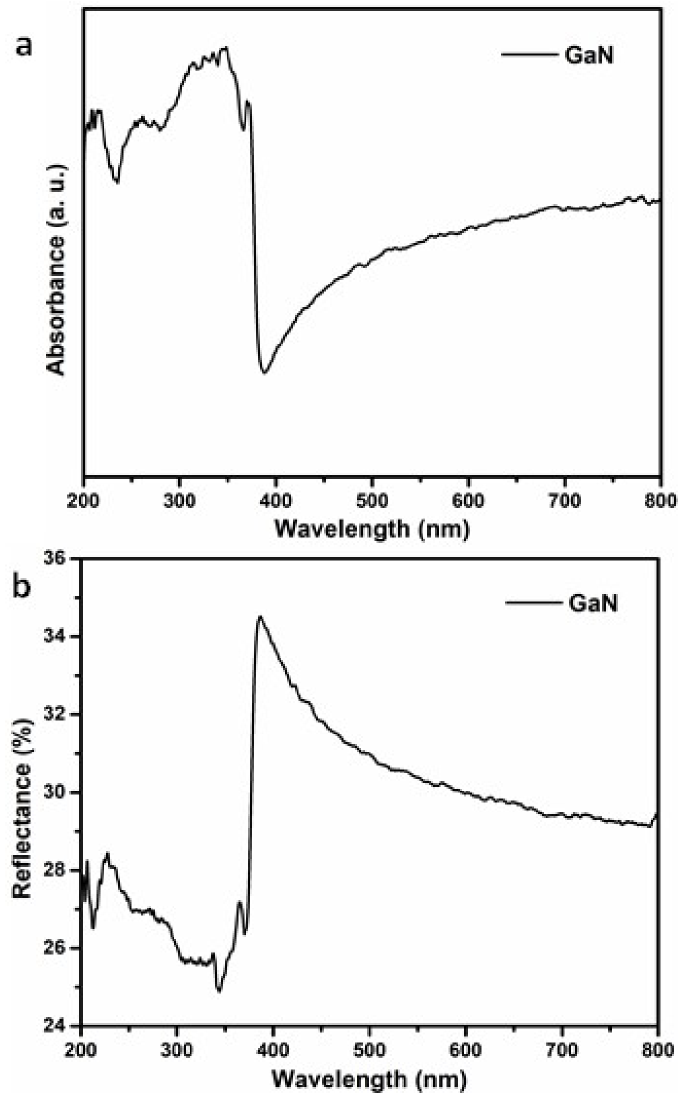

Fig. S3 (a) UV–vis absorption spectrum and (b) diffuse reflectance spectrum of a GaN wafer. The continuous absorption from 400 to 800 nm should result from the solid sample holder with a black back-side support.

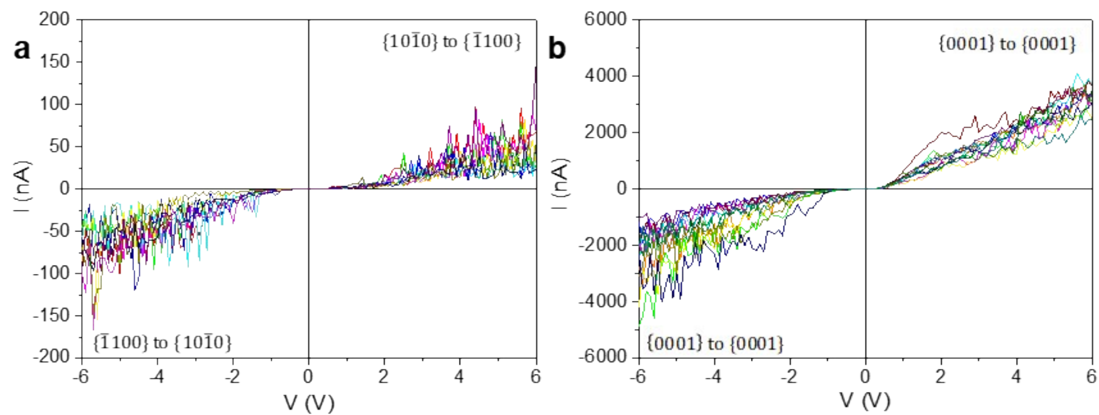

Fig. S4 Multiple *I*–*V* curves recorded with tungsten probes contacting (a) {10$\bar{1}$0}/{$\bar{1}$100} and (b) {0001} surfaces of an intrinsic GaN wafer.

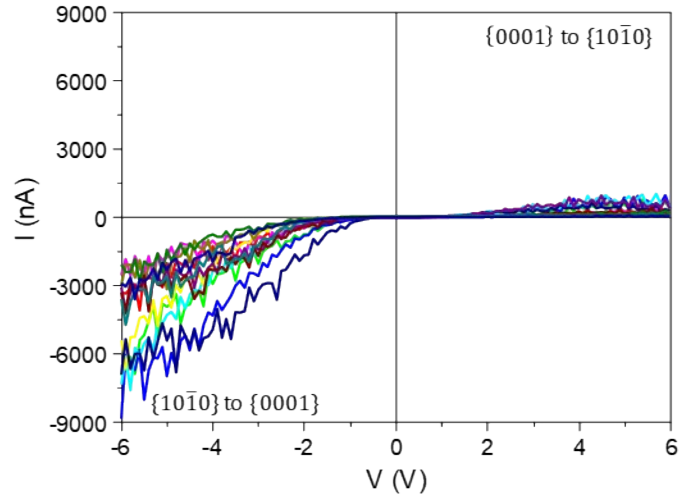

Fig. S5 Multiple *I–V* curves recorded with tungsten probes simultaneously contacting the {10$\bar{1}$0} and {0001} surfaces of an intrinsic GaN wafer.

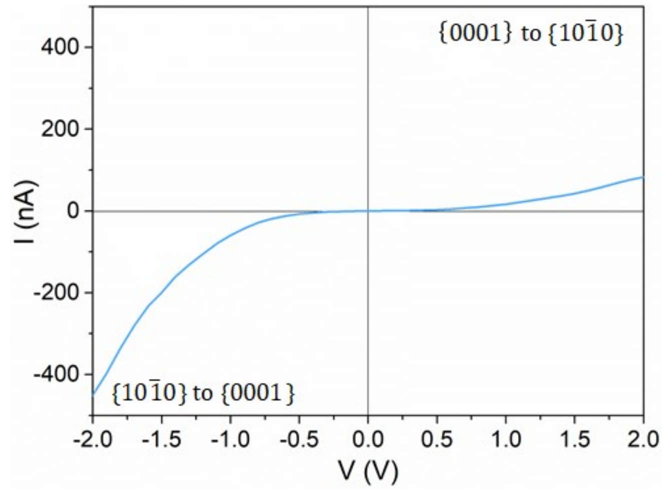

Fig. S6 Expanded *I–V* curve with tungsten probes contacting both {10$\bar{1}$0} and {0001} faces of a GaN wafer.